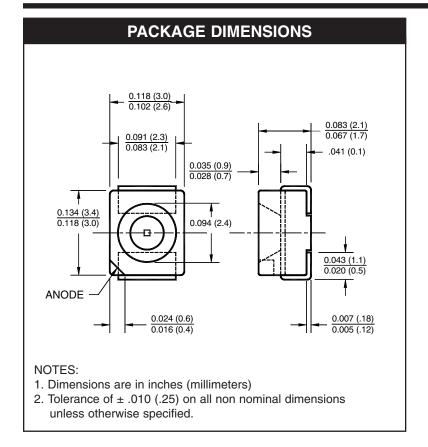
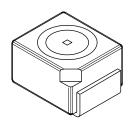
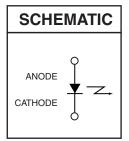
SURFACE MOUNT INFRARED LIGHT EMITTING DIODE

QEB441







DESCRIPTION

The QEB441 is a 730 nm AlGaAs LED encapsulated in a PLCC-2 package.

FEATURES

- λ= 730 nm
- Chip Material: AlGaAs double heterojunction
- Surface Mount PLCC-2 package
- Wide Emission Angle, 120°
- High Power
- Tape and Reel option: .TR



SURFACE MOUNT INFRARED LIGHT EMITTING DIODE

QEB441

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise specified)							
Parameter	Symbol	Rating	Unit				
Operating Temperature	T _{OPR}	-55 to +100	°C				
Storage Temperature	T _{STG}	-55 to +100	°C				
Soldering Temperature (Flow)(2,3)	T _{SOL}	260 for 10 sec	°C				
Continuous Forward Current	I _F	100	mA				
Peak Forward Current ⁽⁴⁾	I _{FP}	1	A				
Reverse Voltage	V _R	5	V				
Power Dissipation ⁽¹⁾	P _D	180	mW				

NOTES

- 1. Derate power dissipation linearly TBD mW/°C above 25°C.
- 2. RMA flux is recommended.
- 3. Methanol or isopropyl alcohols are recommended as cleaning agents.
- 4. Pulse conditions: tp = 100 μ s, T = 10 ms.

ELECTRICAL / OPTICAL CHARACTERISTICS (TA =25°C)								
PARAMETER	TEST CONDITIONS	SYMBOL	MIN.	TYP.	MAX.	UNITS		
Forward Voltage	$I_F = 10 \text{ mA}, \text{ tp} = 20 \text{ ms}$		_	_	2.0	V		
	$I_F = 100 \text{ mA}, \text{ tp} = 20 \text{ ms}$	V _F	_	2.1	_			
	$I_F = 500 \text{ mA}, \text{ tp} = 1 \text{ ms}$.,	_	3.9	4.5			
	$I_F = 1A$, tp = 100 μ s		_	5.5	_			
Emission Angle	I _F = 100 mA	201/ ₂	_	120	_	%		
Reverse Leakage Current	V _R = 5 V	I _R	_	_	10	μA		
Peak Emission Wavelength	I _F = 100 mA	λ_{P}	710	730	750	nm		
Spectral Bandwidth	I _F = 100 mA	$\Delta \lambda$	_	25	_	nm		
Radiant Intensity	$I_F = 100 \text{ mA}, \text{ tp} = 20 \text{ ms}$		2	3	6	mW/sr		
	$I_F = 500 \text{ mA}, \text{ tp} = 1 \text{ ms}$	le	9	14	28			
	$I_F = 1 \text{ A, tp} = 100 \ \mu\text{s}$		16	24	48			
Response Time	$I_F = 10 \text{ mA}, \text{ tp} = 100 \ \mu\text{s}, \text{ T} = 10 \text{ ms}$	t _{r,} t _f	_	_	100	ns		



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Fig.1 Relative Radiant Intensity vs. Input Current

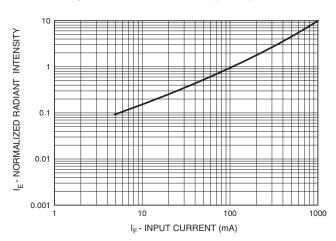


Fig.2 Forward Current vs. Forward Voltage

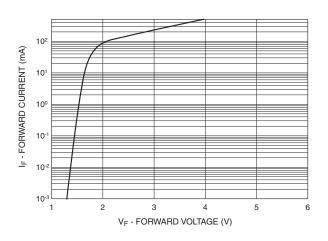


Fig.3 Radiation Diagram

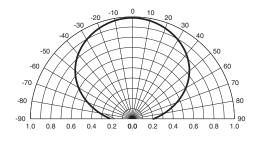


Fig.4 Forward Voltage vs. Ambient Temperature

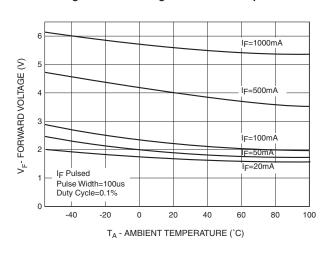
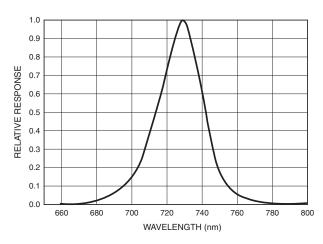


Fig.5 Spectral Response





SURFACE MOUNT INFRARED LIGHT EMITTING DIODE

QEB441

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